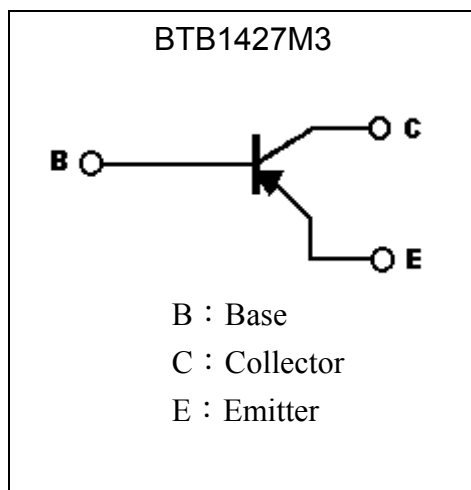
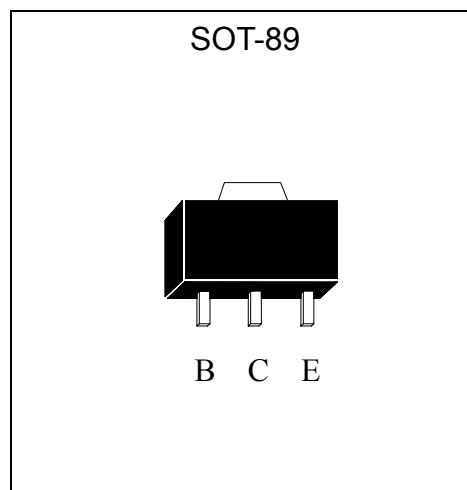


**Low Vcesat PNP Epitaxial Planar Transistor**

# BTB1427M3

**Features**

- Low  $V_{CE(sat)}$ ,  $V_{CE(sat)} = -0.6$  V (typical), at  $I_C / I_B = -4A / -0.1A$
- Excellent DC current gain characteristics

**Symbol**

**Outline**

**Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CBO}$	-20	V
Collector-Emitter Voltage	$V_{CEO}$	-15	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Collector Current	$I_C$	-5	A
	$I_{CP}$	-10 (Note 1)	
Power Dissipation	$P_d$	0.5	W
	$P_d$	2 (Note 2)	
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55~+150	$^\circ\text{C}$

 Note : 1. Single Pulse  $P_w = 10\text{ms}$ 

 2. When mounted on a  $40 \times 40 \times 0.7$  mm ceramic board.

**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CB0</sub>	-20	-	-	V	I <sub>C</sub> =-50μA, I <sub>E</sub> =0
BV <sub>CEO</sub>	-15	-	-	V	I <sub>C</sub> =-1mA, I <sub>B</sub> =0
BV <sub>EBO</sub>	-6	-	-	V	I <sub>E</sub> =-50μA, I <sub>C</sub> =0
I <sub>CB0</sub>	-	-	-0.5	μA	V <sub>CB</sub> =-20V, I <sub>E</sub> =0
I <sub>EBO</sub>	-	-	-0.5	μA	V <sub>EB</sub> =-5V, I <sub>C</sub> =0
*V <sub>CE(sat)</sub>	-	-	-1.0	V	I <sub>C</sub> =-4A, I <sub>B</sub> =-0.1A
*h <sub>FE</sub>	120	-	560	-	V <sub>CE</sub> =-2V, I <sub>C</sub> =-0.5A
f <sub>T</sub>	-	120	-	MHz	V <sub>CE</sub> =-6V, I <sub>C</sub> =-50mA, f=30MHz
C <sub>ob</sub>	-	60	-	pF	V <sub>CB</sub> =-20V, f=1MHz

\*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

**Classification Of h<sub>FE</sub>**

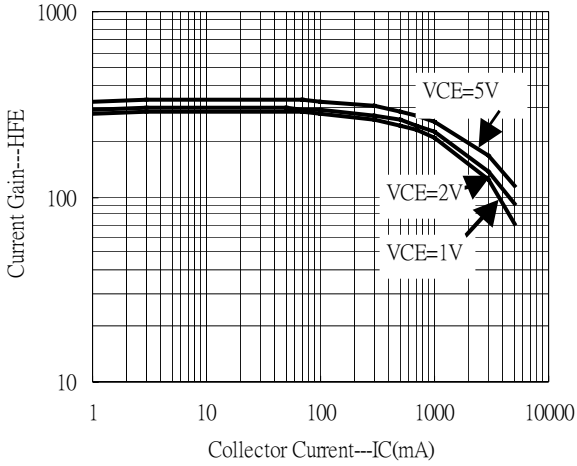
Rank	Q	R	S
Range	120~270	180~390	270~560

**Ordering Information**

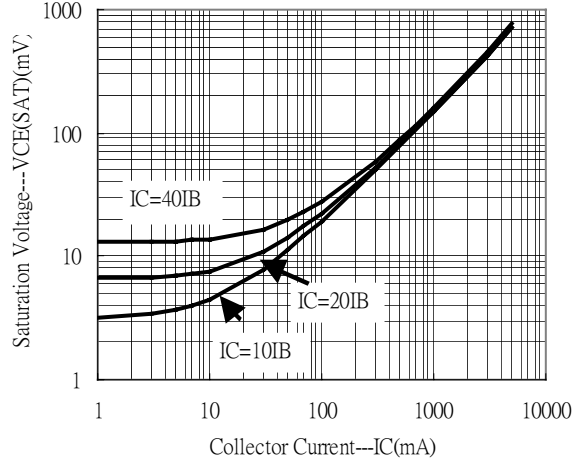
Device	Package	Shipping	Marking
BTB1386M3	SOT-89	1000 pcs / Tape & Reel	BH

**Characteristic Curves**

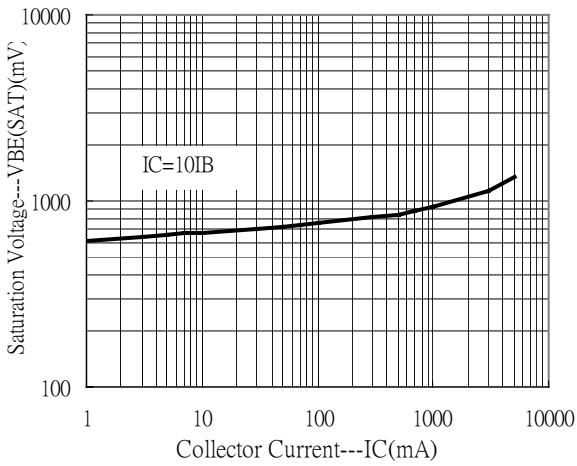
Current Gain vs Collector Current



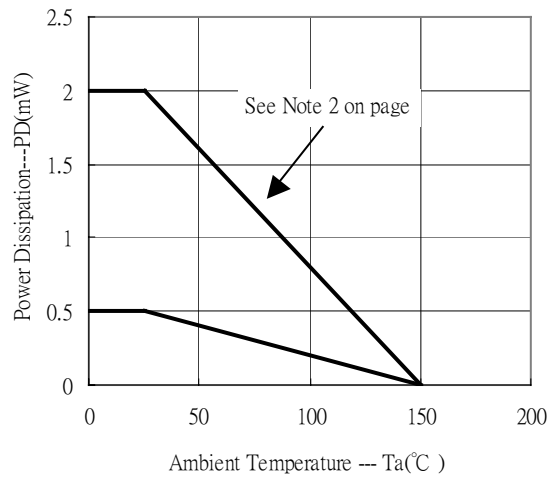
Saturation Voltage vs Collector Current



Saturation Voltage vs Collector Current

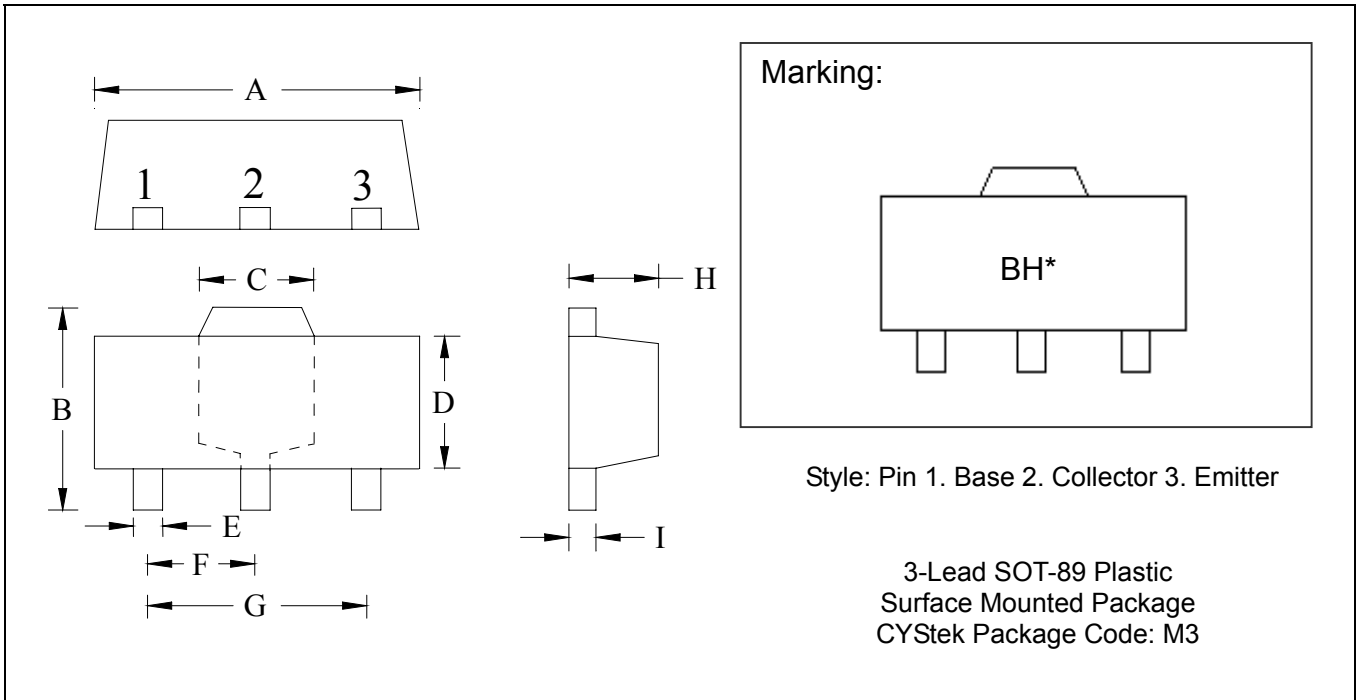


Power Derating Curve





**SOT-89 Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1732	0.1811	4.40	4.60	F	0.0583	0.0598	1.48	1.527
B	0.1594	0.1673	4.05	4.25	G	0.1165	0.1197	2.96	3.04
C	0.0591	0.0663	1.50	1.70	H	0.0551	0.0630	1.40	1.60
D	0.0945	0.1024	2.40	2.60	I	0.0138	0.0161	0.35	0.41
E	0.01417	0.0201	0.36	0.51					

- Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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